

## NANOSECOND PULSED

## INFRARED DIODE LASER AT 830nm

RN-NS-830/1~120mW

### 产品描述

This series laser products with excellent material removal rate, are widely used in microelectronics, material processing, solar energy and medical equipment manufacturing, etc.

### 产品参数

RN-NS-830/1~120mW	
Central wavelength (nm)	830±10
Output power@3.3VDC (mW, CW)	>1, 10, 20, ...,120
Pulse width (FWHM)	>10ns, 20ns, ...,10ms
Transverse mode	Near TEM <sub>00</sub>
Noise of amplitude(rms, CW)	<1%
M <sup>2</sup> factor	<1.5
Beam diameter at the aperture (1/e <sup>2</sup> ,mm)	~3.0
Beam divergence, full angle (mrad)	<1.0
User trigger frequency (Multifunctional Pulse Trigger optional)	1Hz-20MHz(1Hz-20MHz by using CNI Multifunctional Pulse Trigger)
Rise Time (ns)	<3
Fall Time (ns)	<3
Modulation Depth (extinction ratio)	>1000000:1
Warm-up time (minutes)	<5
Beam height from base plate (mm)	19
Operating temperature (°C)	10~35
Input voltage	+12VDC
Expected lifetime (hours)	10000
Warranty	1 year

